

# Anton Gutakovskii

## List of Publications by Citations

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231  
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#	Paper	IF	Citations
222	Normal-incidence infrared photoconductivity in Si p-i-n diode with embedded Ge self-assembled quantum dots. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 1413-1415	3.4	101
221	Magnetic field-induced dissipation-free state in superconducting nanostructures. <i>Nature Communications</i> , <b>2013</b> , 4, 1437	17.4	75
220	Closed curved graphite-like structures formation on micron-size diamond. <i>Chemical Physics Letters</i> , <b>1998</b> , 289, 353-360	2.5	50
219	Effect of quantum confinement on optical properties of Ge nanocrystals in GeO <sub>2</sub> films. <i>Semiconductors</i> , <b>2005</b> , 39, 1168	0.7	46
218	Atomic and energy structure of InAs/AlAs quantum dots. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	42
217	Synthesis and Characterization of Cu <sub>x</sub> S (x = 1/2) Nanocrystals Formed by the Langmuir-Blodgett Technique. <i>Journal of Physical Chemistry C</i> , <b>2014</b> , 118, 23409-23414	3.8	40
216	Application of high-resolution electron microscopy for visualization and quantitative analysis of strain fields in heterostructures. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , <b>2007</b> , 71, 1426-1432	0.4	33
215	Exciton recombination dynamics in an ensemble of (In,Al)As/AlAs quantum dots with indirect band-gap and type-I band alignment. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	30
214	Properties of extremely thin silicon layer in silicon-on-insulator structure formed by smart-cut technology. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2000</b> , 73, 82-86	3.1	28
213	Mechanism of induced nucleation of misfit dislocations in the Ge-on-Si(0 0 1) system and its role in the formation of the core structure of edge misfit dislocations. <i>Acta Materialia</i> , <b>2013</b> , 61, 617-621	8.4	23
212	Ge/Si quantum dot nanostructures grown with low-energy ion beam-assisted epitaxy. <i>Surface and Coatings Technology</i> , <b>2005</b> , 196, 25-29	4.4	23
211	LiVPO <sub>4</sub> F/Li <sub>3</sub> V <sub>2</sub> (PO <sub>4</sub> ) <sub>3</sub> nanostructured composite cathode materials prepared via mechanochemical way. <i>Journal of Solid State Electrochemistry</i> , <b>2014</b> , 18, 1389-1399	2.6	22
210	Mechanisms of edge-dislocation formation in strained films of zinc blende and diamond cubic semiconductors epitaxially grown on (001)-oriented substrates. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 123519	2.5	22
209	Apoptosis-mediated endothelial toxicity but not direct calcification or functional changes in anti-calcification proteins defines pathogenic effects of calcium phosphate bions. <i>Scientific Reports</i> , <b>2016</b> , 6, 27255	4.9	22
208	GeSi films with reduced dislocation density grown by molecular-beam epitaxy on compliant substrates based on porous silicon. <i>Applied Physics Letters</i> , <b>1999</b> , 75, 4118-4120	3.4	21
207	High quality relaxed GaAs quantum dots in GaP matrix. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 023108	3.4	20
206	Plastic relaxation of solid GeSi solutions grown by molecular-beam epitaxy on the low temperature Si(100) buffer layer. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 4710-4714	2.5	20

205	Enhancement of the Si p-n diode NIR photoresponse by embedding $\beta$ -FeSi <sub>2</sub> nanocrystallites. <i>Scientific Reports</i> , <b>2015</b> , 5, 14795	4.9	19
204	Strain relaxation of GeSi/Si(001) heterostructures grown by low-temperature molecular-beam epitaxy. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 7665-7674	2.5	19
203	Direct observations of dislocation half-loops inserted from the surface of the GeSi heteroepitaxial film. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 6140-6142	3.4	19
202	Solid solutions GeSi grown by MBE on a low temperature Si (001) buffer layer: specific features of plastic relaxation. <i>Thin Solid Films</i> , <b>2001</b> , 392, 98-106	2.2	19
201	High resolution electron microscopy of semiconductor interfaces. <i>Physica Status Solidi A</i> , <b>1995</b> , 150, 127-140		19
200	Charge Berezinskii-Kosterlitz-Thouless transition in superconducting NbTiN films. <i>Scientific Reports</i> , <b>2018</b> , 8, 4082	4.9	18
199	Potentialities and basic principles of controlling the plastic relaxation of GeSi/Si and Ge/Si films with stepwise variation in the composition. <i>Semiconductors</i> , <b>2008</b> , 42, 1-20	0.7	18
198	Surface-enhanced Raman spectroscopy of semiconductor nanostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2016</b> , 75, 210-222	3	17
197	Atomic structure and energy spectrum of Ga(As,P)/GaP heterostructures. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 083713	2.5	17
196	Pseudomorphic GeSiSn, SiSn and Ge layers in strained heterostructures. <i>Nanotechnology</i> , <b>2018</b> , 29, 154004	0.4	16
195	Features of formation and propagation of 60° and 90° misfit dislocations in Ge <sub>x</sub> Si <sub>1-x</sub> Bi (x~0.40.5) films caused by Si substrate misorientation from (001). <i>Applied Physics Letters</i> , <b>2008</b> , 92, 131901	3.4	16
194	Heterostructures Ge <sub>x</sub> Si <sub>1-x</sub> /Si(001) (x=0.180.62) grown by molecular beam epitaxy at a low (350 °C) temperature: specific features of plastic relaxation. <i>Thin Solid Films</i> , <b>2004</b> , 466, 69-74	2.2	16
193	Fluorinated graphene suspension for flexible and printed electronics: Flakes, 2D films, and heterostructures. <i>Materials and Design</i> , <b>2019</b> , 164, 107526	8.1	16
192	The convenient preparation of stable aryl-coated zerovalent iron nanoparticles. <i>Beilstein Journal of Nanotechnology</i> , <b>2015</b> , 6, 1192-8	3	15
191	InAs-based metal-oxide-semiconductor structure formation in low-energy Townsend discharge. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 173501	3.4	14
190	Precise surface measurements at the nanoscale. <i>Measurement Science and Technology</i> , <b>2010</b> , 21, 054004	2	14
189	Formation of edge misfit dislocations in Ge <sub>x</sub> Si <sub>1-x</sub> (x~0.40.5) films grown on misoriented (001)->(111) Si substrates. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 3422-3427	1.6	14
188	Optical vibration modes in (Cd, Pb, Zn)S quantum dots in the Langmuir-Blodgett matrix. <i>Physics of the Solid State</i> , <b>2002</b> , 44, 1976-1980	0.8	14

187	The influence of irradiation and subsequent annealing on Si nanocrystals formed in SiO <sub>2</sub> layers. <i>Semiconductors</i> , <b>2000</b> , 34, 965-970	0.7	14
186	The formation of partial misfit dislocations during heteroepitaxy. <i>Physica Status Solidi A</i> , <b>1981</b> , 67, 299-304		14
185	Linear chains of Ge/Si quantum dots grown on a prepatterned surface formed by ion irradiation. <i>Semiconductors</i> , <b>2015</b> , 49, 749-752	0.7	13
184	Preparation of thin films of platinum group metals by pulsed MOCVD. I. Deposition of Ir layers. <i>Journal of Structural Chemistry</i> , <b>2012</b> , 53, 715-724	0.9	13
183	Initial stage growth of Ge <sub>x</sub> Si <sub>1-x</sub> layers and Ge quantum dot formation on Ge <sub>x</sub> Si <sub>1-x</sub> surface by MBE. <i>Nanoscale Research Letters</i> , <b>2012</b> , 7, 561	5	13
182	CdZnS quantum dots formed by the Langmuir-Blodgett technique. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2013</b> , 31, 04D109	1.3	13
181	Strong sensitivity of photoluminescence of InAs/AlAs quantum dots to defects: evidence for lateral inter-dot transport. <i>Semiconductor Science and Technology</i> , <b>2006</b> , 21, 527-531	1.8	13
180	Sb as surfactant at plastic relaxation of GeSi/Si(001) films grown by molecular-beam epitaxy: Reduction of surface roughness value. <i>Journal of Crystal Growth</i> , <b>2006</b> , 297, 57-60	1.6	13
179	Growth and structure of Ge nanoislands on an atomically clean silicon oxide surface. <i>Physics of the Solid State</i> , <b>2004</b> , 46, 77-79	0.8	13
178	Oxide-free InAs(111)A interface in metal-oxide-semiconductor structure with very low density of states prepared by anodic oxidation. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 161601	3.4	12
177	The mechanism of {113} defect formation in silicon: clustering of interstitial-vacancy pairs studied by in situ high-resolution electron microscope irradiation. <i>Microscopy and Microanalysis</i> , <b>2013</b> , 19 Suppl 5, 38-42	0.5	12
176	Growth, structure and luminescence properties of multilayer Si/FeSi <sub>2</sub> NCs/Si/Si nanoheterostructures. <i>Thin Solid Films</i> , <b>2011</b> , 519, 8480-8484	2.2	12
175	Pulsed ion-beam induced nucleation and growth of Ge nanocrystals on SiO <sub>2</sub> . <i>Applied Physics Letters</i> , <b>2007</b> , 90, 133120	3.4	12
174	Heterostructures Ge <sub>x</sub> Si <sub>1-x</sub> /Si(0 0 1) grown by low-temperature (300-400 °C) molecular beam epitaxy: Misfit dislocation propagation. <i>Journal of Crystal Growth</i> , <b>2005</b> , 280, 309-319	1.6	12
173	Hemozoin "knobs" in <i>Opisthorchis felinus</i> infected liver. <i>Parasites and Vectors</i> , <b>2015</b> , 8, 459	4	11
172	Initial stages of Ge epitaxy on Si(111) under quasi-equilibrium growth conditions. <i>JETP Letters</i> , <b>2010</b> , 92, 388-395	1.2	11
171	Specific features of formation and propagation of 60° and 90° misfit dislocations in Ge <sub>x</sub> Si <sub>1-x</sub> /Si films with x>0.4. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 3080-3084	1.6	11
170	Effect of ion dose and annealing mode on photoluminescence from SiO <sub>2</sub> implanted with Si ions. <i>Semiconductors</i> , <b>1998</b> , 32, 1222-1228	0.7	11

169	The formation of silicon nanocrystals in SiO <sub>2</sub> layers by the implantation of Si ions with intermediate heat treatments. <i>Semiconductors</i> , <b>2005</b> , 39, 552-556	0.7	11
168	Interface phonons in semiconductor nanostructures with quantum dots. <i>Journal of Experimental and Theoretical Physics</i> , <b>2005</b> , 101, 554-561	1	11
167	A room-temperature-operated Si LED with $\beta$ -FeSi <sub>2</sub> nanocrystals in the active layer: $\lambda$ emission power at 1.5 $\mu$ m. <i>Journal of Applied Physics</i> , <b>2017</b> , 121, 113101	2.5	10
166	Different electrochemical responses of LiFe <sub>0.5</sub> Mn <sub>0.5</sub> PO <sub>4</sub> prepared by mechanochemical and solvothermal methods. <i>Journal of Alloys and Compounds</i> , <b>2018</b> , 742, 454-465	5.7	10
165	Evolution of silicon nanoclusters and hydrogen in SiN <sub>x</sub> :H films: Influence of high hydrostatic pressure under annealing. <i>Thin Solid Films</i> , <b>2012</b> , 520, 6207-6214	2.2	10
164	Dislocation interaction of layers in the Ge/Ge-seed/GexSi <sub>1-x</sub> /Si(0 0 1) (x ~ 0.30.5) system: Trapping of misfit dislocations on the Ge-seed/GeSi interface. <i>Acta Materialia</i> , <b>2013</b> , 61, 5400-5405	8.4	10
163	Crystallization of amorphous Si nanoclusters in SiO(x) films using femtosecond laser pulse annealings. <i>Journal of Nanoscience and Nanotechnology</i> , <b>2012</b> , 12, 8694-9	1.3	10
162	Study of Onion-Like Carbon (OLC) Formation from Ultra Disperse Diamond (UDD). <i>Materials Research Society Symposia Proceedings</i> , <b>1994</b> , 359, 105		10
161	Defects in the crystal structure of Cd x Hg <sub>1-x</sub> Te layers grown on the Si (310) substrates. <i>Semiconductors</i> , <b>2011</b> , 45, 926-934	0.7	9
160	Formation of edge misfit dislocations in GexSi <sub>1-x</sub> (x~0.40.8) films grown on misoriented (001)->(111) Si substrates: Features before and after film annealing. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 123521	2.5	9
159	Nonradiative energy transfer between vertically coupled indirect and direct bandgap InAs quantum dots. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 263102	3.4	9
158	Dominating nucleation of misfit dislocations from the surface in GeSi/Si(0 0 1) films with a stepwise composition grown by means of molecular-beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2006</b> , 293, 247-252	1.6	9
157	Enhanced strain relaxation in a two-step process of GexSi <sub>1-x</sub> /Si(001) heterostructures grown by low-temperature molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 4599-4601	3.4	9
156	Electrical conductivity of silicon-on-insulator structures prepared by bonding silicon wafers to a substrate using hydrogen implantation. <i>Semiconductors</i> , <b>2000</b> , 34, 1054-1057	0.7	9
155	Splitting and electrical properties of the SOI structure formed from the heavily boron doped silicon with using of the smart-cut technology. <i>Microelectronic Engineering</i> , <b>1999</b> , 48, 383-386	2.5	9
154	Study of InGaAs/GaAs strained-layer superlattices by TEM and RBS techniques. <i>Physica Status Solidi A</i> , <b>1989</b> , 115, 413-425		9
153	Influence of the additional p+ doped layers on the properties of AlGaAs/InGaAs/AlGaAs heterostructures for high power SHF transistors. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 095108	3	9
152	Heterostructures with diffused interfaces: Luminescent technique for ascertainment of band alignment type. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 115701	2.5	8

151	Quantum dots formed in InSb/AlAs and AlSb/AlAs heterostructures. <i>JETP Letters</i> , <b>2016</b> , 103, 692-698	1.2	8
150	Aluminum-induced crystallization of silicon suboxide thin films. <i>Applied Physics A: Materials Science and Processing</i> , <b>2018</b> , 124, 1	2.6	8
149	Novel self-assembled quantum dots in the GaSb/AlAs heterosystem. <i>JETP Letters</i> , <b>2012</b> , 95, 534-536	1.2	8
148	Defects and their Electronic Properties in High-Pressure-Annealed SOI Structures Sliced by Hydrogen <b>2002</b> , 269-288		8
147	Probing the Mg <sub>2</sub> Si/Si(1 1 1) heterojunction for photovoltaic applications. <i>Solar Energy</i> , <b>2020</b> , 211, 383-395	8	
146	Atomic and electronic structure of ferroelectric La-doped HfO <sub>2</sub> films. <i>Materials Research Express</i> , <b>2019</b> , 6, 036403	1.7	8
145	Peculiarities of structure, morphology, and electrochemistry of the doped 5-V spinel cathode materials LiNi <sub>0.5-x</sub> Mn <sub>1.5-y</sub> M <sub>x+y</sub> O <sub>4</sub> (M = Co, Cr, Ti; x+y = 0.05) prepared by mechanochemical way. <i>Journal of Solid State Electrochemistry</i> , <b>2016</b> , 20, 235-246	2.6	7
144	Dual threshold diode based on the superconductor-to-insulator transition in ultrathin TiN films. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 042601	3.4	7
143	Formation of iron and iron silicides on silicon and iron surfaces. Role of the deposition rate and volumetric effects. <i>Applied Physics A: Materials Science and Processing</i> , <b>2013</b> , 112, 507-515	2.6	7
142	Photoluminescence associated with {113} defects in oxygen-implanted silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1700317	1.6	7
141	Preparation of thin films of platinum group metals by pulsed MOCVD. II. Deposition of Ru layers. <i>Journal of Structural Chemistry</i> , <b>2012</b> , 53, 725-733	0.9	7
140	New system of self-assembled GaSb/GaP quantum dots. <i>Semiconductors</i> , <b>2012</b> , 46, 1534-1538	0.7	7
139	MODIFICATION OF GROWTH MODE OF Ge ON Si BY PULSED LOW-ENERGY ION-BEAM IRRADIATION. <i>International Journal of Nanoscience</i> , <b>2004</b> , 03, 19-27	0.6	7
138	Formation of nanocrystalline silicon films using high-dose H <sup>+</sup> ion implantation into silicon-on-insulator layers with subsequent rapid thermal annealing. <i>Semiconductors</i> , <b>2004</b> , 38, 107-112	0.7	7
137	Instability of the distribution of atomic steps on Si(111) upon submonolayer gold adsorption at high temperatures. <i>JETP Letters</i> , <b>2005</b> , 81, 117-121	1.2	7
136	In Situ HREM Irradiation Study of an Intrinsic Point Defects Clustering in FZ-Si. <i>Crystal Research and Technology</i> , <b>2000</b> , 35, 775-786	1.3	7
135	Defect Formation during MBE Growth of CdTe (111). <i>Physica Status Solidi A</i> , <b>1991</b> , 126, 181-188		7
134	On the structure and photoluminescence of dislocations in silicon. <i>Journal of Applied Physics</i> , <b>2018</b> , 124, 053106	2.5	6

133	Optically detected magnetic resonance of photoexcited electrons in (In,Al)As/AlAs quantum dots with indirect band gap and type-I band alignment. <i>Physical Review B</i> , <b>2018</b> , 97,	3.3	6
132	High-precision nanoscale length measurement. <i>Nanotechnologies in Russia</i> , <b>2013</b> , 8, 518-531	0.6	6
131	High-quality single-crystal diamond-graphite-diamond membranes and devices. <i>International Journal of Nanotechnology</i> , <b>2015</b> , 12, 226	1.5	6
130	Morphological transformations of vanadium oxide films during low-temperature reduction in hydrogen electron cyclotron resonance plasma. <i>Journal of Surface Investigation</i> , <b>2007</b> , 1, 454-461	0.5	6
129	Bimetallic Pt,Ir-containing coatings formed by MOCVD for medical applications. <i>Journal of Materials Science: Materials in Medicine</i> , <b>2019</b> , 30, 69	4.5	5
128	Raman, AFM, and TEM profiling of QD multilayer structures. <i>Materials Research Express</i> , <b>2015</b> , 2, 035003	1.7	5
127	Fluorinated graphene nanoparticles with 1-3 nm electrically active graphene quantum dots. <i>Nanotechnology</i> , <b>2020</b> , 31, 295602	3.4	5
126	A new approach to the fabrication of VO nanoswitches with ultra-low energy consumption. <i>Nanoscale</i> , <b>2020</b> , 12, 3443-3454	7.7	5
125	Specific features of plastic relaxation of a metastable Ge x Si1 lx layer buried between a silicon substrate and a relaxed germanium layer. <i>Physics of the Solid State</i> , <b>2014</b> , 56, 247-253	0.8	5
124	Formation of Mg silicides on amorphous Si. Origin and role of high pressure in the film growth. <i>Materials Chemistry and Physics</i> , <b>2014</b> , 148, 1078-1082	4.4	5
123	Coexistence of type-I and type-II band alignment in Ga(Sb, P)/GaP heterostructures with pseudomorphic self-assembled quantum dots. <i>JETP Letters</i> , <b>2014</b> , 99, 76-81	1.2	5
122	Ferromagnetic HfO2/Si/GaAs interface for spin-polarimetry applications. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 123506	3.4	5
121	Pulsed ion-beam assisted deposition of Ge nanocrystals on SiO2 for non-volatile memory device. <i>Thin Solid Films</i> , <b>2008</b> , 517, 313-316	2.2	5
120	InP decomposition phosphorus beam source for MBE: design, properties and superlattice growth. <i>Semiconductor Science and Technology</i> , <b>2003</b> , 18, 417-422	1.8	5
119	Formation of ultrasmall germanium nanoislands with a high density on an atomically clean surface of silicon oxide. <i>Physics of the Solid State</i> , <b>2005</b> , 47, 67	0.8	5
118	Strained multilayer structures with pseudomorphic GeSiSn layers. <i>Semiconductors</i> , <b>2016</b> , 50, 1584-1588	0.7	5
117	Intrinsic Point Defect Clustering in Si: A Study by HVEM and HREM in Situ Electron Irradiation <b>1997</b> , 63-92		5
116	GaAs/GaP Quantum-Well Heterostructures Grown on Si Substrates. <i>Semiconductors</i> , <b>2019</b> , 53, 1143-1147	0.7	4



115	Analysis of the dislocation structure at the Ge/Si(111) heterointerface. <i>Journal of Surface Investigation</i> , <b>2014</b> , 8, 787-793	0.5	4
114	Structural state of Ge/Si heterosystems with (001), (111), and (7 7 10) interfaces. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , <b>2012</b> , 76, 325-327	0.4	4
113	Structure and Optical Properties of Ca Silicide Films and Si/Ca <sub>3</sub> Si <sub>4</sub> /Si(111) Heterostructures. <i>Solid State Phenomena</i> , <b>2014</b> , 213, 71-79	0.4	4
112	Edge misfit dislocations in the GeSi/Si(001) pair: Conditions and specific features of high-quantity generation. <i>Journal of Crystal Growth</i> , <b>2012</b> , 338, 12-15	1.6	4
111	Influence of shape of GaN/AlN quantum dots on luminescence decay law. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2012</b> , 209, 653-656	1.6	4
110	Spontaneous composition modulation during Cd x Hg <sub>1-x</sub> Te(301) molecular beam epitaxy. <i>JETP Letters</i> , <b>2011</b> , 94, 324-328	1.2	4
109	Strained germanium films in Ge/InGaAs/GaAs heterostructures: Formation of edge misfit dislocations at the Ge/InGaAs interface. <i>Physics of the Solid State</i> , <b>2011</b> , 53, 2005-2011	0.8	4
108	Investigation of multilayer silicon structures with buried iron silicide nanocrystallites: growth, structure, and properties. <i>Journal of Nanoscience and Nanotechnology</i> , <b>2008</b> , 8, 527-34	1.3	4
107	Plastic relaxation of GeSi/Si(001) films grown by molecular-beam epitaxy in the presence of the Sb surfactant. <i>Semiconductors</i> , <b>2007</b> , 41, 1234-1239	0.7	4
106	Origination of misfit dislocations at the surface during the growth of GeSi/Si(001) films by low-temperature (300±00°C) molecular-beam epitaxy. <i>Semiconductors</i> , <b>2006</b> , 40, 319-326	0.7	4
105	Epitaxial silicon films deposited at high rates by gas-jet electron beam plasma CVD. <i>Surface and Coatings Technology</i> , <b>2003</b> , 174-175, 1178-1181	4.4	4
104	Defects in silicon heat-treated under uniform stress and irradiated with fast neutrons. <i>Physica Status Solidi A</i> , <b>2003</b> , 199, 207-213		4
103	Structure of cadmium and lead sulfide nanoclusters in a matrix of a langmuir-blodgett film. <i>Journal of Structural Chemistry</i> , <b>1999</b> , 40, 485-487	0.9	4
102	Formation and crystal structure of GaSb/GaP quantum dots. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , <b>2016</b> , 80, 17-22	0.4	4
101	Unexpected travel of Lomer-type dislocations in Ge/GexSi <sub>1-x</sub> /Si(001) heterostructures. <i>Thin Solid Films</i> , <b>2016</b> , 616, 348-350	2.2	4
100	Formation of a Thin Continuous GaSb Film on Si(001) by Solid Phase Epitaxy. <i>Nanomaterials</i> , <b>2018</b> , 8,	5.4	4
99	Transformation of the InP(001) surface upon annealing in an arsenic flux. <i>Surface Science</i> , <b>2021</b> , 710, 121861	1.8	4
98	Self-assembled strained GeSiSn nanoscale structures grown by MBE on Si(100). <i>Journal of Crystal Growth</i> , <b>2017</b> , 457, 215-219	1.6	3



97	Structure of Hf <sub>0.9</sub> La <sub>0.1</sub> O <sub>2</sub> Ferroelectric Films Obtained by the Atomic Layer Deposition. <i>JETP Letters</i> , <b>2019</b> , 109, 116-120	1.2	3
96	Electron-nuclei interaction in the X valley of (In,Al)As/AlAs quantum dots. <i>Physical Review B</i> , <b>2020</b> , 101,	3.3	3
95	Electron Microscopy Study of Metal Sulfide Nanocrystals Formed in Langmuir-Blodgett Films. <i>Nanotechnologies in Russia</i> , <b>2017</b> , 12, 369-375	0.6	3
94	Influence of a Low-Temperature GaAs Dislocation Filter on the Perfection of GaAs/Si Layers. <i>Optoelectronics, Instrumentation and Data Processing</i> , <b>2018</b> , 54, 181-186	0.6	3
93	Resistive Switching Effect with ON/OFF Current Relation up to 10 <sup>9</sup> in 2D Printed Composite Films of Fluorinated Graphene with V <sub>2</sub> O <sub>5</sub> Nanoparticles. <i>Advanced Electronic Materials</i> , <b>2019</b> , 5, 1900310	6.4	3
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91	Brief observe on iron silicide growth on amorphous silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2013</b> , 10, 1742-1745		3
90	Surface-enhanced Raman scattering by semiconductor nanostructures. <i>Optoelectronics, Instrumentation and Data Processing</i> , <b>2013</b> , 49, 504-513	0.6	3
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